



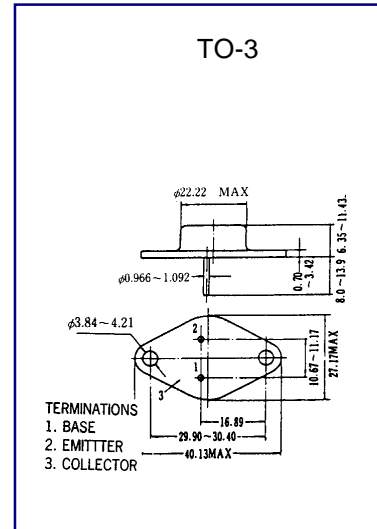
MJ13335

NPN SILICON TRANSISTORS

HIGH VOLTAGE SILICON HIGH POWER TRANSISTORS
SOLENOID AND RELAY DRIVERS

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	800	V
Collector-Emitter Voltage	VCEO	500	V
Collector Current (DC)	IC	20	A
Collector Dissipation (Tc=25°C)	Pc	175	W
Junction Temperature	Tj	200	°C
Storage Temperature	Tstg	-50~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	ICBO	V _{CB} = 800V , I _E =0			250	μA
Collector Cutoff Current	ICEO	V _{CB} = 500V , I _B =0			250	μA
DC Current Gain	h _{FE}	V _{CE} = 5V , I _C =5.0A	10		60	
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C =10A , I _B =2A			1.8	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =10A , I _B =2A			1.8	